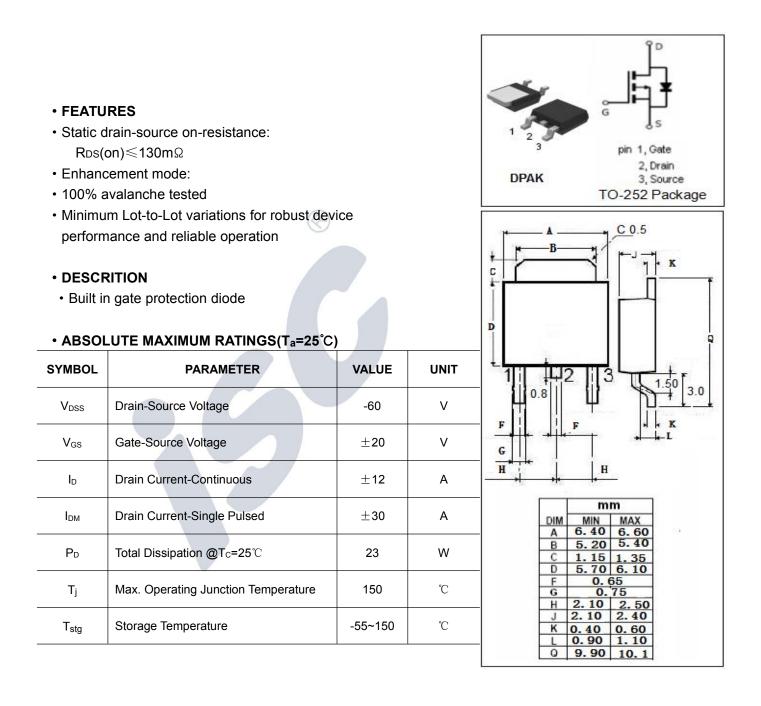


isc P-Channel MOSFET Transistor

2SJ598



1



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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =1mA	-60			v
V _{GS} (th)	Gate Threshold Voltage	VDS=-10V; ID=1mA	-1.5		-2.5	v
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =-10V; I _D =-6A			130	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±16V;V _{DS} = 0V			±10	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-60V; V _{GS} = 0V			-10	μA
V _{SD}	Diode forward voltage	IF=12A, V _{GS} = 0V		0.98		V

NOTICE:

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